

L Number	Hits	Search Text	DB	Time stamp
10	1238	118/52.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:09
11	1379	118/52,501.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:18
12	916	118/52,501.ccls. and (rotary or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:29
13	469	((118/52,501.ccls. and (rotary or rotat\$3)) and vertical\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:29
14	385	((118/52,501.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:25
15	48	((118/52,501.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)) and ((collect\$3 or recover\$3) near2 (waste or liquid or fluid))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:30
16	2129	118/52,320,321,501.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:19
17	47	118/52,320,321,501.ccls. and (trough)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:19
20	1284	118/52,320,321,501.ccls. and (rotary or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:25
21	685	(118/52,320,321,501.ccls. and (rotary or rotat\$3)) and vertical\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:25
22	457	((118/52,320,321,501.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:25
23	51	((118/52,320,321,501.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)) and ((collect\$3 or recover\$3) near2 (waste or liquid or fluid))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:27
24	754	156/345.11,345.18,345.19,345.51,345.55.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:29

25	18	156/345.11,345.18,345.19,345.51,345.55.ccls. and trough	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:29
26	300	156/345.11,345.18,345.19,345.51,345.55.ccls. and (rotary or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:29
27	189	(156/345.11,345.18,345.19,345.51,345.55.ccls. and (rotary or rotat\$3)) and vertical\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:30
28	18	((156/345.11,345.18,345.19,345.51,345.55.ccls. and (rotary or rotat\$3)) and vertical\$2) and ((collect\$3 or recover\$3) near2 (waste or liquid or fluid))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:30
-	5	(hideyuki near2 murooka).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:42
-	41	(masato near2 tsuchiya).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:40
-	16	(shunichi near2 ogasawara).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:41
-	5	(hideyuki near2 murooka).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:42
-	61	(Mimasu adj Semiconductor).as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:44
-	3806	134/95.2,95.3,102.3,104.2,149,153,157,902.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:51
-	1627	134/95.2,95.3,102.3,104.2,149,153,157,902.ccls. and (rotary or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:09
-	1009	(134/95.2,95.3,102.3,104.2,149,153,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:09
-	692	((134/95.2,95.3,102.3,104.2,149,153,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:10

-	139	((((134/95.2,95.3,102.3,104.2,149,153,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)) and ((collect\$3 or recover\$3) near2 (waste or liquid or fluid))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/14 13:10
-	4570	134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:51
-	1813	134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (rotary or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:56
-	1120	(134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:51
-	716	((134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:52
-	152	((((134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)) and ((collect\$3 or recover\$3) near2 (waste or liquid or fluid))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:58
-	25	134/104.2.ccls. and (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 12:13
-	10	134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (annular adj trough)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:57
-	9	438/\$.ccls. and (annular adj trough)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:57
-	205	((((134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)) and annular	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 11:58
-	17	134/104.2.ccls. and (annular)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 12:02
-	210	134/104.2.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 12:19
-	59	134/104.2.ccls. and (rotary or rota\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 12:19

-	0	134/\$.ccls. and (semiconductor or wafer or substrate) and (waste near2 trough)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 13:46
-	9	134/\$.ccls. and (semiconductor or wafer or substrate) and (annular near2 trough)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 13:50
-	142	(semiconductor or wafer or substrate) and (annular near2 trough)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 13:47
-	96	((semiconductor or wafer or substrate) and (annular near2 trough)) and (rotary or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 13:48
-	0	134/\$.ccls. and (semiconductor or wafer or substrate) and ((annular near2 trough) with vertical\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 13:55